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physics, the almost "handbook"-like and very modern pre-sentation provided in the book under review appears to be very sensible. VLSI technology: fundamentals and applications Yu. V. Gulyaev an Yud. L. Kopylov Usp. Fiz. Nauk 156, 552-553 (November 1988) Y. Tarui. VLSI Technology: Fundamentals and Appli-cations, (Ed.).

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This book focuses on conceptual frameworks that are helpful in understanding the basics of electronics – what the feedback system is, the principle of an oscillator, the operational working of an amplifier, and other relevant topics. It also provides an overview of the technologies supporting electronic systems, like OP-AMP, transistor, filter, ICs, and diodes. It consists of seven chapters, written in an easy and understandable language, and featuring relevant block diagrams, circuit diagrams, valuable and interesting solved examples, and important test questions. Further, the book includes up-to-date illustrations, exercises, and numerous worked examples to illustrate the theory and to demonstrate their use in practical designs.

This book covers the physics of semiconductors on an introductory level, assuming that the reader already has some knowledge of condensed matter physics. Crystal structure, band structure, carrier transport, phonons, scattering processes and optical properties are presented for typical semiconductors such as silicon, but III–V and II–VI compounds are also included. In view of the increasing importance of wide-gap semiconductors, the electronic and optical properties of these materials are dealt with too.

To surmount the continuous scaling challenges of MOSFET devices, FinFETs have emerged as the real alternative for use as the next generation device for IC fabrication technology. The objective of this book is to provide the basic theory and operating principles of FinFET devices and technology, an overview of FinFET device architecture and manufacturing processes, and detailed formulation of FinFET electrostatic and dynamic device characteristics for IC design and manufacturing. Thus, this book caters to practicing engineers transitioning to FinFET technology and prepares the next generation of device engineers and academic experts on mainstream device technology at the nanometer-nodes.

Resistivity -- Carrier and doping density -- Contact resistance and Schottky barriers -- Series resistance, channel length and width, and threshold voltage -- Defects -- Oxide and interface trapped charges, oxide thickness -- Carrier lifetimes -- Mobility -- Charge-based and probe characterization -- Optical characterization -- Chemical and physical characterization -- Reliability and failure analysis.

Modern Semiconductor Devices for Integrated Circuits, First Edition introduces readers to the world of modern semiconductor devices with an emphasis on integrated circuit applications. KEY TOPICS: Electrons and Holes in Semiconductors; Motion and Recombination of Electrons and Holes; Device Fabrication Technology; PN and Metal–Semiconductor Junctions; MOS Capacitor; MOS Transistor; MOSFETs in ICs—Scaling, Leakage, and Other Topics; Bipolar Transistor. MARKET: Written by an experienced teacher, researcher, and expert in industry practices, this succinct and forward-looking text is appropriate for anyone interested in semiconductor devices for integrated circuits, and serves as a suitable reference text for practicing engineers.

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